

Epitaxial Planar NPN Transistor

MJD3055

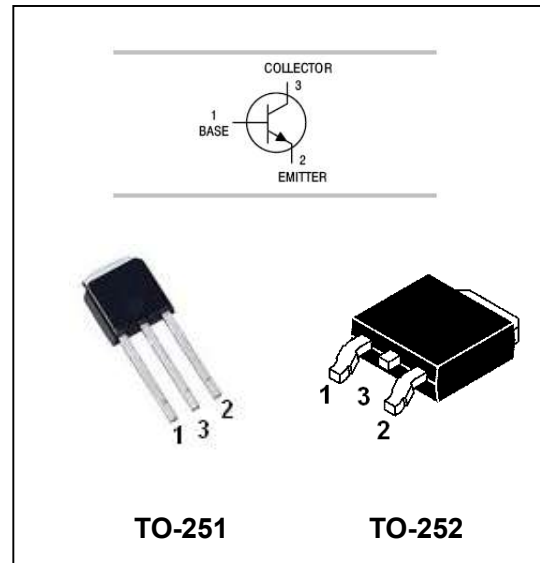
FEATURES

- Lead formed for surface mount applications.
- Straight lead.
- Electrically similar to popular MJE3055T.
- DC current gain specified to 10A.



APPLICATIONS

- Low speed switching applications.
- D-PAK for surface mount applications.



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Volage	70	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	10	A
I_B	Base Current	6	A
P_C	Collector Power Dissipation	20	W
T_j, T_{stg}	Junction and Storage temperature range	-55 to +150	°C

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ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-emitter sustaining voltage	$V_{CEO(sus)}$	$I_C=30\text{mA}, I_B=0$	60	-	V
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{V}, I_B=0$	-	50	μA
Collector cut-off current	I_{CBO}	$V_{CB}=70\text{V}, I_E=0$	-	2	mA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$	-	0.5	mA
DC current gain	h_{FE}	$V_{CE}=4\text{V}, I_C=4\text{A}$ $V_{CE}=4\text{V}, I_C=10\text{A}$	20 5	100 -	-
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=4\text{A}, I_B=0.4\text{A}$ $I_C=10\text{A}, I_B=3.3\text{A}$	-	1.1 8	V
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE}=4\text{V}, I_C=4\text{A}$	-	1.8	V
Current gain bandwidth product	f_T	$V_{CE}=10\text{V}, I_C=0.5\text{A}$	2	-	MHz

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

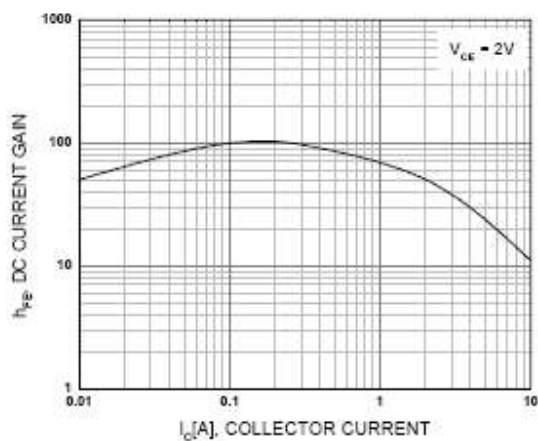


Figure 1. DC current Gain

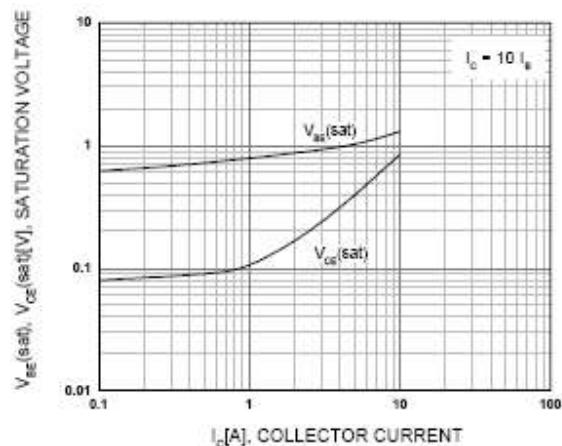


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

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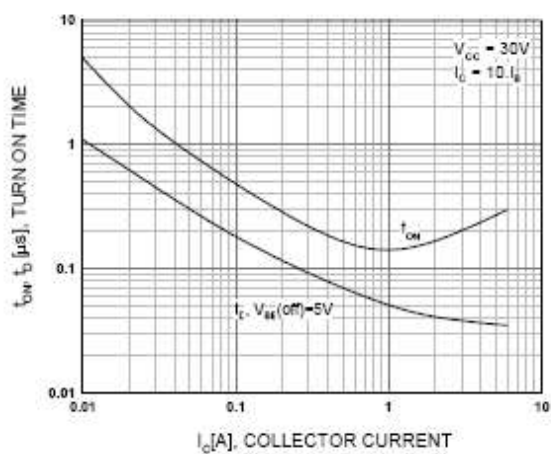


Figure 3. Turn On Time

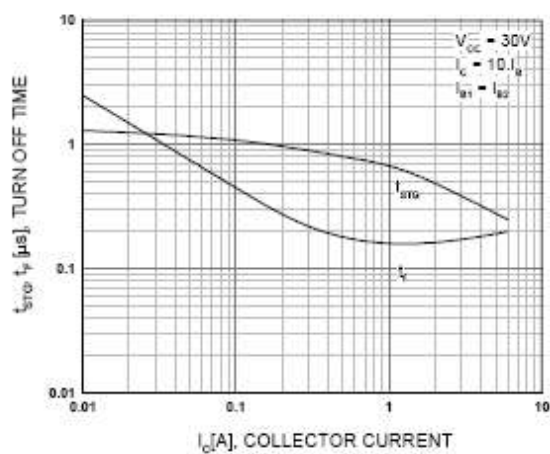


Figure 4. Turn Off Time

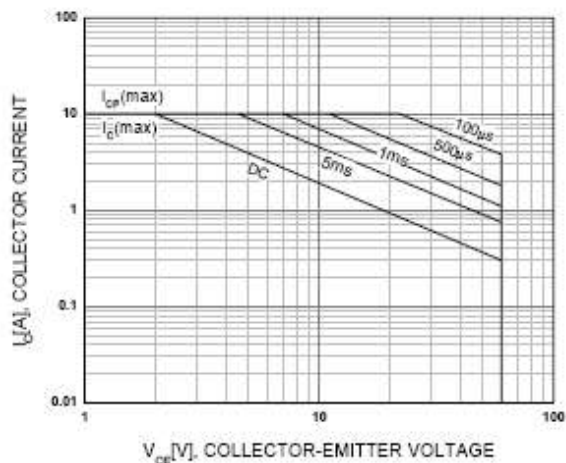


Figure 5. Safe Operating Area

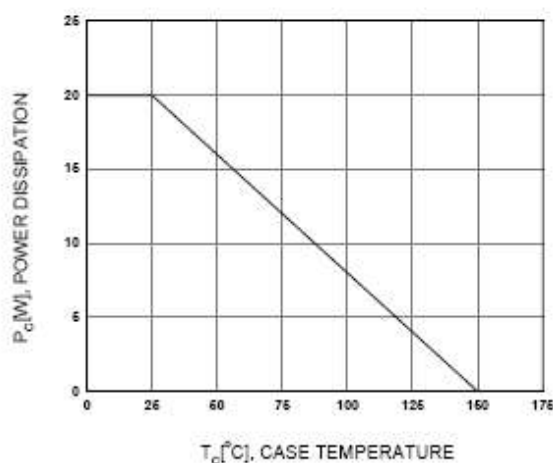


Figure 6. Power Derating

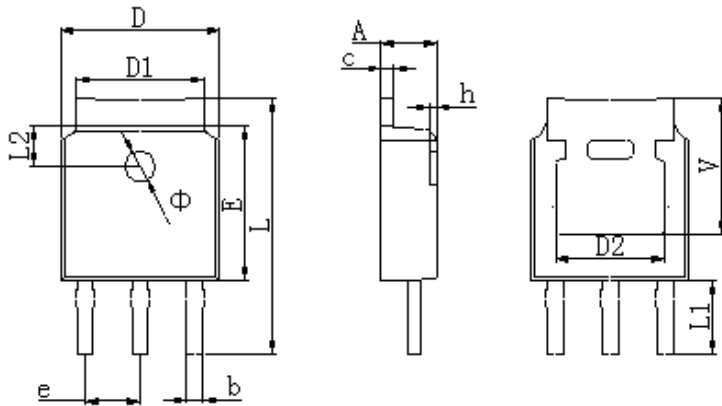
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PACKAGE OUTLINE

Plastic surface mounted package

TO-251

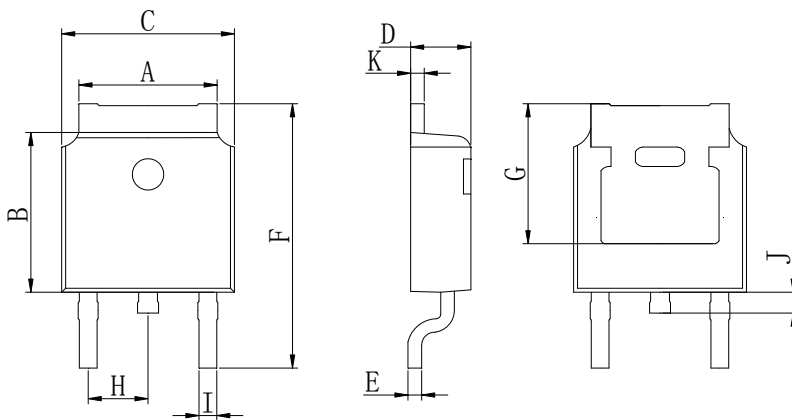


TO-251		
A	2.200	2.400
b	0.500	0.700
c	0.460	0.580
D	6.500	6.700
D1	5.100	5.460
D2	4.830 Typ.	
E	6.000	6.200
e	2.186	2.386
L	12.000	12.600
L1	5.100 Typ.	
L2	1.400	1.700
Φ	1.100	1.300
h	0.000	0.300
V	5.350 Typ.	
All Dimensions in mm		

PACKAGE OUTLINE

Plastic surface mounted package

TO-252

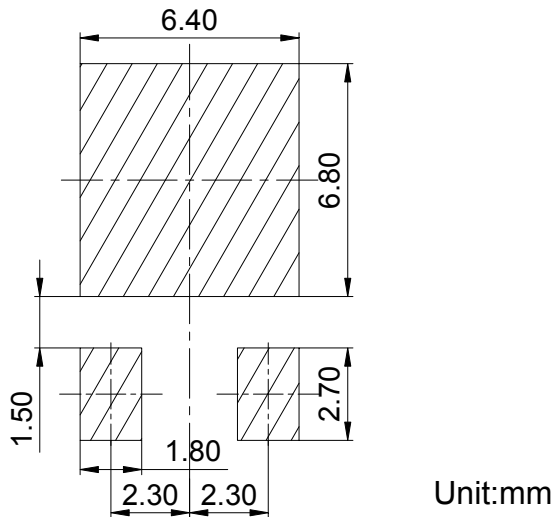


TO-252		
A	4.95	5.59
B	5.40	6.63
C	6.05	7.10
D	2.20	2.40
E	0.40	0.61
F	8.80	10.60
G	5.35 Typ.	
H	1.98	2.59
I	0.50	0.90
J	0.50	1.20
K	0.45	0.89
All Dimensions in mm		

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SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MJD3055	TO-251/252	80PCS/Tube
	TO-252	2500PCS/Tape&Reel